

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L11	1	'two gate electrode' and undoped near oxide and ('subatmospheric-chemical vapor deposited 'SA-C10/919555 and 10/954400D') near ('BPSG' 'boron and phosphorous-doped silicon oxide) and gap.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/01 14:42

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S71	5	("6080639").URPN.	USPAT	OR	OFF	2005/11/01 13:05
S72	13	("5182221" "6030881" "6080639" "6261957" "6297128" "6306722" "6319796" "6323102" "6329261" "6376391" "6410446" "6432797" "6531377").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/11/01 13:13
S73	13	("5182221" "6030881" "6080639" "6261957" "6297128" "6306722" "6319796" "6323102" "6329261" "6376391" "6410446" "6432797" "6531377").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/11/01 13:16
S74	4	("5621241" "5679606" "5716890" "5968610").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/11/01 13:22
S78	7718	(257/295,298,314-326).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/01 14:45
S79	995	(floating adj gate) with dielectric with (ONO (oxide near nitride near oxide))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/01 14:50
S80	19358	BPSG PBSG (phosphorous near boron near (silicate silicon adj oxide) near glass)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/01 14:49
S81	2	S79 with S80	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/01 14:51
S82	2766	(floating adj gate) and dielectric with (ONO (oxide near nitride near oxide))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/01 14:50
S83	426	S82 and S80	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/01 14:50

S84	11	S79 same S80	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/01 14:56
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